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CZ (utility model), CZ, DE (utility model), DE, DK (utility model), DK, DM, DZ, EC, EE (utility model), EE, ES, FI (utility model), FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK (utility model), SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZM, ZW.

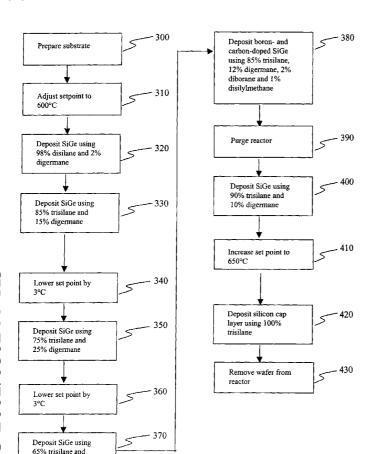
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(54) Title: IMPROVED PROCESS FOR DEPOSITION OF SEMICONDUCTOR FILMS

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(57) Abstract: Chemical vapor deposition processes utilize chemical precursors that allow for the deposition of thin films to be conducted at or near the mass transport limited regime. The processes have high deposition rates yet produce more uniform films, both compositionally and in thickness, than films prepared using conventional chemical precursors. In preferred embodiments, trisilane is employed to deposit thin films containing silicon useful in the semiconductor industry in various applications such as transistor gate electrodes.



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⁵tn ional Application No

PCT/US 02/02921 A. CLASSIFICATION OF SUBJECT MATTER IPC 7 H01L21/205 C23C16/00 C30B25/02 According to International Patent Classification (IPC) or to both national classification and IPC **B. FIELDS SEARCHED** Minimum documentation searched (classification system followed by classification symbols) H01L C23C C30B Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched Electronic data base consulted during the international search (name of data base and, where practical, search terms used) EPO-Internal, PAJ, WPI Data C. DOCUMENTS CONSIDERED TO BE RELEVANT Relevant to claim No. Citation of document, with indication, where appropriate, of the relevant passages Category ° PATENT ABSTRACTS OF JAPAN 1,4-9, Х 13, vol. 1996, no. 01, 31 January 1996 (1996-01-31) & JP 07 249618 A (FUJITSU LTD; OTHERS: 01), 26 September 1995 (1995-09-26) 16-18, 20-23, 27-29. 35,37, 78-80,83 abstract 12,26 Α -/--Further documents are listed in the continuation of box C. Patent family members are listed in annex. X | X | ° Special categories of cited documents: "T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the "A" document defining the general state of the art which is not considered to be of particular relevance invention "E" earlier document but published on or after the international filling date "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled "O" document referring to an oral disclosure, use, exhibition or other means "P" document published prior to the international filing date but later than the priority date claimed "&" document member of the same patent family Date of mailing of the international search report Date of the actual completion of the international search 13 11 2003 28 July 2003 Authorized officer Name and mailing address of the ISA European Patent Office, P.B. 5818 Patentlaan 2 NL - 2280 HV Rijswijk Tel. (+31-70) 340-2040, Tx. 31 651 epo nl, Fax: (+31-70) 340-3016

Voignier, V.

It tional Application No
PCT/US 02/02921

C.(Continu	iation) DOCUMENTS CONSIDERED TO BE RELEVANT	
Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	PATENT ABSTRACTS OF JAPAN vol. 017, no. 375 (E-1397), 14 July 1993 (1993-07-14) & JP 05 062911 A (FUJITSU LTD), 12 March 1993 (1993-03-12)	1,2, 6-10,13, 16,17, 20-22, 24, 27-29, 31,35, 37,38
A	abstract; figure 1	18,19, 23,25
X	PATENT ABSTRACTS OF JAPAN vol. 017, no. 160 (E-1342), 29 March 1993 (1993-03-29) & JP 04 323834 A (SEIKO EPSON CORP), 13 November 1992 (1992-11-13) abstract	1,3,14, 15, 35-37, 39,74
Α	abstract	16,30, 32,34
X	PATENT ABSTRACTS OF JAPAN vol. 2000, no. 02, 29 February 2000 (2000-02-29) & JP 11 317530 A (SEMICONDUCTOR ENERGY LAB CO LTD), 16 November 1999 (1999-11-16)	1,3-9, 14,16, 20-23, 27,28, 30,32, 33,35, 37,39,40
x	abstract US 5 227 329 A (HASHIMOTO TAKASHI ET AL) 13 July 1993 (1993-07-13)	1,8,9, 12,14, 15, 35-37, 40,66-69
A	column 2, line 22 - line 29 column 5, line 35 - line 43; figures 3,7,8; examples 3,4	16, 26-28, 30,33,34
(US 5 214 002 A (HAYASHI YUTAKA ET AL) 25 May 1993 (1993-05-25)	1-4, 6-11,13, 14,16, 20, 22-25, 27-33,
1	the whole document	35,37-40 66,68-71

rnational application No. PCT/US 02/02921

Box I	Observations where certain claims were found unsearchable (Continuation of item 1 of first sheet)
This Inte	ernational Search Report has not been established in respect of certain claims under Article 17(2)(a) for the following reasons:
1.	Claims Nos.: because they relate to subject matter not required to be searched by this Authority, namely:
2. X	Claims Nos.: - because they relate to parts of the International Application that do not comply with the prescribed requirements to such an extent that no meaningful International Search can be carried out, specifically:
3.	Claims Nos.: because they are dependent claims and are not drafted in accordance with the second and third sentences of Rule 6.4(a).
Box II	Observations where unity of invention is lacking (Continuation of item 2 of first sheet)
This Inter	rnational Searching Authority found multiple inventions in this international application, as follows:
	see additional sheet
1.	As all required additional search fees were timely paid by the applicant, this International Search Report covers all searchable claims.
2.	As all searchable claims could be searched without effort justifying an additional fee, this Authority did not invite payment of any additional fee.
3.	As only some of the required additional search fees were timely paid by the applicant, this International Search Report covers only those claims for which fees were paid, specifically claims Nos.:
4. X	No required additional search fees were timely paid by the applicant. Consequently, this International Search Report is restricted to the invention first mentioned in the claims; it is covered by claims Nos.: $1-40,66-83$
Remark o	The additional search fees were accompanied by the applicant's protest. No protest accompanied the payment of additional search fees.

FURTHER INFORMATION CONTINUED FROM PCT/ISA/ 210

This International Searching Authority found multiple (groups of) inventions in this international application, as follows:

1. claims: 1-40, 66-83

A process for depositing a Si-containing film on a substrate in a chamber using trisilane.

An apparatus to implement this process.

A coumpound Si-containing film in an integrated circuit.

2. claims: 41-56

A process for depositing a SiGe film on a substrate in a CVD chamber using a gas mixture comprising high-order silane and high order germane.

A SiGe film in an integrated circuit

3. claims: 57-65

A process for depositing, in a CVD chamber, a first Si-containing layer on a substrate at a first controlled temperature using a first gas comprising a first Si-containing precursor, and a second Si-containing layer at a second controlled temperature onto the first Si-containing layer using a second gas comprising a second Si-containing precursor.

Information on patent family members

li tional Application No
PCT/US 02/02921

Patent document cited in search report		Publication date	Patent family member(s)		Publication date
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